Kuan-Chang Chang

List of Publications by Year
in descending order

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157 papers	3,818 citations	109264 35 h-index	161767 54 g-index
160 all docs	160 docs citations	160 times ranked	2592 citing authors

#	Article	IF	Citations
1	Offset-Compensation High-Performance Sense Amplifier for Low-Voltage DRAM Based on Current Mirror and Switching Point. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 2011-2015.	2.2	3
2	Analysis of Carrier Behavior for Amorphous Indium Gallium Zinc Oxide After Supercritical Carbon Dioxide Treatment. Advanced Materials Interfaces, 2022, 9, .	1.9	1
3	Compact and Fast Response Dual-Directional SCR for Nanoscale ESD Protection Engineering. IEEE Transactions on Electron Devices, 2022, 69, 3490-3493.	1.6	3
4	The observation of Gaussian distribution and origination identification of deep defects in AlGaN/GaN MIS-HEMT. Applied Physics Letters, 2022, 120, 172107.	1.5	0
5	Low-temperature supercritical activation enables high-performance detection of cell-free DNA by all-carbon-nanotube transistor. Carbon, 2022, 196, 120-127.	5.4	7
6	Performance enhancement and mechanism exploration of all-carbon-nanotube memory with hydroxylation and dehydration through supercritical carbon dioxide. Carbon, 2021, 173, 97-104.	5.4	11
7	Suppression of Statistical Variability in Junctionless FinFET Using Accumulation-Mode and Charge Plasma Structure. IEEE Transactions on Electron Devices, 2021, 68, 399-404.	1.6	6
8	Visible-light-stimulated synaptic InGaZnO phototransistors enabled by wavelength-tunable perovskite quantum dots. Nanoscale Advances, 2021, 3, 5046-5052.	2.2	13
9	Low-temperature supercritical dehydroxylation for achieving an ultra-low subthreshold swing of thin-film transistors. Nanoscale, 2021, 13, 5700-5705.	2.8	8
10	Achieving complementary resistive switching and multi-bit storage goals by modulating the dual-ion reaction through supercritical fluid-assisted ammoniation. Nanoscale, 2021, 13, 14035-14040.	2.8	7
11	Performance Enhancement and Bending Restoration for Flexible Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors by Low-Temperature Supercritical Dehydration Treatment. ACS Applied Materials & Interfaces, 2021, 13, 8584-8594.	4.0	20
12	Pâ€1.11: Performance Improvement of aâ€IGZO Thinâ€Film Transistor By Using Ta 2 O 5 /SiO 2 Doubleâ€layer Gate Dielectric. Digest of Technical Papers SID International Symposium, 2021, 52, 440-442.	0.1	0
13	Supercritical Fluid of Amorphous-silicon Flexible Thin-film Transistors. , 2021, , .		0
14	Interfacial Modification of Thin Film Transistor via Supercritical Fluids Treatment and Mechanism Exploration. , 2021, , .		0
15	An Effective Method for Improving the Insulating Property of Polyvinyl Alcohol in Device with Supercritical Fluids. , 2021, , .		0
16	Supercritical Ammoniation-Enabled Interfacial Polarization for Function-Mode Transformation and Overall Optimization of Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 40053-40061.	4.0	3
17	Manipulation of epsilon-near-zero wavelength for the optimization of linear and nonlinear absorption by supercritical fluid. Scientific Reports, 2021, 11, 15936.	1.6	9
18	Novel Symmetrical Dual-Directional SCR With p-Type Guard Ring for High-Voltage ESD Protection. IEEE Transactions on Electron Devices, 2021, 68, 4164-4167.	1.6	3

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19	Ultrasensitive Freestanding and Mechanically Durable Artificial Synapse with Attojoule Power Based on Naâ€Salt Doped Polymer for Biocompatible Neuromorphic Interface. Advanced Functional Materials, 2021, 31, 2106015.	7.8	8
20	HfO₂â€Based Memristor as an Artificial Synapse for Neuromorphic Computing with Triâ€Layer HfO₂/BiFeO₃/HfO₂ Design. Advanced Functional Materials, 2021, 31, 2107131.	7.8	63
21	Bifunctional homologous alkali-metal artificial synapse with regenerative ability and mechanism imitation of voltage-gated ion channels. Materials Horizons, 2021, 8, 3072-3081.	6.4	6
22	Ultrasensitive Freestanding and Mechanically Durable Artificial Synapse with Attojoule Power Based on Naâ€Salt Doped Polymer for Biocompatible Neuromorphic Interface (Adv. Funct. Mater. 42/2021). Advanced Functional Materials, 2021, 31, 2170313.	7.8	0
23	Eco-Friendly, Highly Efficient Ethanol-Assisted Supercritical Preparation of an Ultrathin ZnO Nanotube. ACS Sustainable Chemistry and Engineering, 2021, 9, 15478-15483.	3.2	2
24	An indirect way to achieve comprehensive performance improvement of resistive memory: when hafnium meets ITO in an electrode. Nanoscale, 2020, 12, 3267-3272.	2.8	23
25	A Robust and Lowâ€Power Bismuth Doped Tin Oxide Memristor Derived from Coaxial Conductive Filaments. Small, 2020, 16, e2004619.	5.2	21
26	Variable-temperature activation energy extraction to clarify the physical and chemical mechanisms of the resistive switching process. Nanoscale, 2020, 12, 15721-15724.	2.8	7
27	Performance Improvement of aâ€IGZO Thinâ€Film Transistor By Using Ta 2 O 5 /SiO 2 Doubleâ€layer Gate Dielectric. Digest of Technical Papers SID International Symposium, 2020, 51, 1-3.	0.1	0
28	Unveiling the influence of surrounding materials and realization of multi-level storage in resistive switching memory. Nanoscale, 2020, 12, 22070-22074.	2.8	8
29	A supercritical removal method: the rapid elimination of impurities in polymethyl-methacrylate at near room temperature and a mechanism investigation of insulating property improvements. Journal of Materials Chemistry C, 2020, 8, 15664-15668.	2.7	10
30	Precise Tuning of Epsilon-Near-Zero Properties in Indium Tin Oxide Nanolayer by Supercritical Carbon Dioxide. , 2020, , .		2
31	Hysteresis-Free, High-Performance Polymer-Dielectric Organic Field-Effect Transistors Enabled by Supercritical Fluid. Research, 2020, 2020, 6587102.	2.8	12
32	Insulating Property Improvement of Polyimide in Devices by Lowâ€Temperature Supercritical Fluids. Advanced Electronic Materials, 2019, 5, 1900580.	2.6	18
33	Improving Performance of All-Carbon-Nanotube Thin-Film Transistors by Low Temperature Supercritical CO₂ Fluid Activation. IEEE Electron Device Letters, 2019, 40, 921-924.	2.2	14
34	Hafnium nanocrystals observed in a HfTiO compound film bring about excellent performance of flexible selectors in memory integration. Nanoscale, 2019, 11, 20792-20796.	2.8	10
35	ZnO/N:ZnO core-shell nanorods prepared via supercritical CO2-N process: Tunable doping and response reversal phenomena for gas sensing. Ceramics International, 2018, 44, 7296-7299.	2.3	4
36	Impact of Forming Compliance Current on Storage Window Induced by a Gadolinium Electrode in Oxide-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2018, 65, 96-100.	1.6	10

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37	Exploration of highly enhanced performance and resistive switching mechanism in hafnium doping ZnO memristive device. Semiconductor Science and Technology, 2018, 33, 085013.	1.0	13
38	An Investigation of Anode Hole Injection-Induced Abnormal Body Current in n-Channel HfO₂/TiN MOSFETs. IEEE Journal of the Electron Devices Society, 2018, 6, 803-807.	1.2	1
39	Schottky Emission Distance and Barrier Height Properties of Bipolar Switching Gd:SiOx RRAM Devices under Different Oxygen Concentration Environments. Materials, 2018, 11, 43.	1.3	25
40	Tuning the nanostructures and optical properties of undoped and N-doped ZnO by supercritical fluid treatment. AIP Advances, 2018, 8, .	0.6	6
41	Resistance Switching Characteristics Induced by O₂ Plasma Treatment of an Indium Tin Oxide Film for Use as an Insulator in Resistive Random Access Memory. ACS Applied Materials & Interfaces, 2017, 9, 3149-3155.	4.0	27
42	Nonvolatile reconfigurable sequential logic in a HfO₂ resistive random access memory array. Nanoscale, 2017, 9, 6649-6657.	2.8	55
43	Influence of Ammonia on Amorphous Carbon Resistive Random Access Memory. IEEE Electron Device Letters, 2017, 38, 453-456.	2.2	10
44	The effect of asymmetrical electrode form after negative bias illuminated stress in amorphous IGZO thin film transistors. Applied Physics Letters, 2017, 110, .	1.5	13
45	Controlling the Degree of Forming Soft-Breakdown and Producing Superior Endurance Performance by Inserting BN-Based Layers in Resistive Random Access Memory. IEEE Electron Device Letters, 2017, 38, 445-448.	2.2	9
46	Role of H₂O Molecules in Passivation Layer of a-InGaZnO Thin Film Transistors. IEEE Electron Device Letters, 2017, 38, 469-472.	2.2	23
47	Surface Engineering of Polycrystalline Silicon for Long-Term Mechanical Stress Endurance Enhancement in Flexible Low-Temperature Poly-Si Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 11942-11949.	4.0	40
48	Analysis of Contrasting Degradation Behaviors in Channel and Drift Regions Under Hot Carrier Stress in PDSOI LD N-Channel MOSFETs. IEEE Electron Device Letters, 2017, 38, 705-707.	2.2	14
49	Attaining resistive switching characteristics and selector properties by varying forming polarities in a single HfO₂-based RRAM device with a vanadium electrode. Nanoscale, 2017, 9, 8586-8590.	2.8	56
50	Effects of plasma treatment time on surface characteristics of indium-tin-oxide film for resistive switching storage applications. Applied Surface Science, 2017, 414, 224-229.	3.1	19
51	Suppression of endurance degradation by applying constant voltage stress in one-transistor and one-resistor resistive random access memory. Japanese Journal of Applied Physics, 2017, 56, 010303.	0.8	14
52	Abnormal Recovery Phenomenon Induced by Hole Injection During Hot Carrier Degradation in SOI n-MOSFETs. IEEE Electron Device Letters, 2017, 38, 835-838.	2.2	2
53	Recovery of failed resistive switching random access memory devices by a low-temperature supercritical treatment. Applied Physics Express, 2017, 10, 064001.	1.1	5
54	The effect of device electrode geometry on performance after hot-carrier stress in amorphous In-Ga-Zn-O thin film transistors with different via-contact structures. Applied Physics Letters, 2017, 110, .	1.5	8

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55	Effect of charge quantity on conduction mechanism of high- and low-resistance states during forming process in a one-transistorâ€“one-resistor resistance random access memory. Applied Physics Express, 2017, 10, 054101.	1.1	11
56	Boosting the performance of resistive switching memory with a transparent ITO electrode using supercritical fluid nitridation. RSC Advances, 2017, 7, 11585-11590.	1.7	21
57	Influence of Thermal Annealing Treatment on Bipolar Switching Properties of Vanadium Oxide Thin-Film Resistance Random-Access Memory Devices. Journal of Electronic Materials, 2017, 46, 2147-2152.	1.0	7
58	Functionally Complete Boolean Logic in 1T1R Resistive Random Access Memory. IEEE Electron Device Letters, 2017, 38, 179-182.	2.2	95
59	Conduction Mechanism and Improved Endurance in HfO2-Based RRAM with Nitridation Treatment. Nanoscale Research Letters, 2017, 12, 574.	3.1	54
60	Investigating degradation behaviors induced by mobile Cu ions under high temperature negative bias stress in a-InGaZnO thin film transistors. Applied Physics Letters, 2017, 111, 133504.	1.5	3
61	Resistive Random Access Memory: Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using Highâ€k Spacer Structure (Adv. Electron. Mater. 9/2017). Advanced Electronic Materials, 2017, 3, .	2.6	0
62	Inert Pt electrode switching mechanism after controlled polarity-forming process in In2O3-based resistive random access memory. Applied Physics Express, 2017, 10, 094102.	1.1	2
63	Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using Highâ€k Spacer Structure. Advanced Electronic Materials, 2017, 3, 1700171.	2.6	19
64	A universal model for interface-type threshold switching phenomena by comprehensive study of Vanadium oxide-based selector. , 2017, , .		1
65	Systematic Analysis of High-Current Effects in Flexible Polycrystalline-Silicon Transistors Fabricated on Polyimide. IEEE Transactions on Electron Devices, 2017, 64, 3167-3173.	1.6	15
66	Impact of repeated uniaxial mechanical strain on flexible a-IGZO thin film transistors with symmetric and asymmetric structures. Applied Physics Letters, 2017, 110, 263505.	1.5	13
67	Super Critical Fluid Technique to Enhance Current Output on Amorphous Silicon-Based Photovoltaic. IEEE Electron Device Letters, 2017, 38, 1401-1404.	2.2	11
68	Organometal tri-halide perovskite resistive switching device with PMMA electrode interlayer. , 2017, , .		0
69	A synaptic device built in one diodeâ€“one resistor (1Dâ€“1R) architecture with intrinsic SiOx-based resistive switching memory. ChemistrySelect, 2016, 1, .	0.7	0
70	Mechanisms of Low-Temperature Nitridation Technology on a TaN Thin Film Resistor for Temperature Sensor Applications. Nanoscale Research Letters, 2016, 11, 275.	3.1	4
71	Engineering interface-type resistance switching based on forming current compliance in ITO/Ga2O3:ITO/TiN resistance random access memory: Conduction mechanisms, temperature effects, and electrode influence. Applied Physics Letters, 2016, 109, .	1.5	21
72	Confirmation of filament dissolution behavior by analyzing electrical field effect during reset process in oxide-based RRAM. Applied Physics Letters, 2016, 109, .	1.5	11

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73	Complementary resistive switching behavior for conductive bridge random access memory. Applied Physics Express, 2016, 9, 064201.	1.1	9
74	Improving Performance by Doping Gadolinium Into the Indium-Tinâ€“Oxide Electrode in HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 584-587.	2.2	28
75	Effects of erbium doping of indium tin oxide electrode in resistive random access memory. Applied Physics Express, 2016, 9, 034202.	1.1	11
76	Effect of different constant compliance current for hopping conduction distance properties of the Sn:SiOx thin film RRAM devices. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	17
77	Modifying Indium-Tin-Oxide by Gas Cosputtering for Use as an Insulator in Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2016, 63, 4288-4294.	1.6	5
78	Adjustable built-in resistor on oxygen-vacancy-rich electrode-capped resistance random access memory. Applied Physics Express, 2016, 9, 104201.	1.1	5
79	Study of high-tech process furnace using inherently safer design strategies (III) advanced thin film process and reduction of power consumption. Journal of Loss Prevention in the Process Industries, 2016, 43, 280-291.	1.7	15
80	Improvement of Bipolar Switching Properties of Gd:SiOx RRAM Devices on Indium Tin Oxide Electrode by Low-Temperature Supercritical CO2 Treatment. Nanoscale Research Letters, 2016, 11, 52.	3.1	12
81	Ultra-Low Switching Voltage Induced by Inserting SiO₂Layer in Indiumâ€“Tinâ€“Oxide-Based Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 1276-1279.	2.2	17
82	Realization of Functional Complete Stateful Boolean Logic in Memristive Crossbar. ACS Applied Materials & Interfaces, 2016, 8, 34559-34567.	4.0	56
83	Ultralow Power Resistance Random Access Memory Device and Oxygen Accumulation Mechanism in an Indiumâ€“Tin-Oxide Electrode. IEEE Transactions on Electron Devices, 2016, 63, 4737-4743.	1.6	15
84	The Film Thickness Effect on Electrical Conduction Mechanisms and Characteristics of the Niâ€“Cr Thin Film Resistor. IEEE Journal of the Electron Devices Society, 2016, 4, 441-444.	1.2	8
85	Obtaining Lower Forming Voltage and Self-Compliance Current by Using a Nitride Gas/Indiumâ€“Tin Oxide Insulator in Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2016, 63, 4769-4775.	1.6	9
86	Reducing operation voltages by introducing a low-kswitching layer in indiumâ€“tin-oxide-based resistance random access memory. Applied Physics Express, 2016, 9, 061501.	1.1	5
87	Illumination Effect on Bipolar Switching Properties of Gd:SiO2 RRAM Devices Using Transparent Indium Tin Oxide Electrode. Nanoscale Research Letters, 2016, 11, 224.	3.1	12
88	Resistive Switching Mechanism of Oxygen-Rich Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 408-411.	2.2	31
89	Rational Hydrogenation for Enhanced Mobility and High Reliability on ZnO-based Thin Film Transistors: From Simulation to Experiment. ACS Applied Materials & Interfaces, 2016, 8, 5408-5415.	4.0	30
90	Bulk Oxygenâ€“Ion Storage in Indiumâ€“Tinâ€“Oxide Electrode for Improved Performance of HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 280-283.	2.2	50

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91	Communicationâ€"Effects of Oxygen Concentration Gradient on Resistive Switching Behavior in Oxygen Vacancy-Rich Electrodes. ECS Journal of Solid State Science and Technology, 2016, 5, Q115-Q118.	0.9	6
92	Resistance random access memory. Materials Today, 2016, 19, 254-264.	8.3	391
93	Influence of nitrogen buffering on oxygen in indium-tin-oxide capped resistive random access memory with NH3 treatment. , 2015, , .		0
94	Complementary resistive switching behavior induced by varying forming current compliance in resistance random access memory. Applied Physics Letters, 2015, 106, .	1.5	45
95	Effects of Varied Negative Stop Voltages on Current Self-Compliance in Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 564-566.	2.2	37
96	Nitrogen Buffering Effect on Oxygen in Indium-Tin-Oxide-Capped Resistive Random Access Memory With NH₃ Treatment. IEEE Electron Device Letters, 2015, 36, 1138-1141.	2.2	13
97	The Manipulation of Temperature Coefficient Resistance of TaN Thin-Film Resistor by Supercritical CO₂ Fluid. IEEE Electron Device Letters, 2015, 36, 271-273.	2.2	4
98	An Electronic Synapse Device Based on Solid Electrolyte Resistive Random Access Memory. IEEE Electron Device Letters, 2015, 36, 772-774.	2.2	24
99	Hopping conduction properties of the Sn:SiO X thin-film resistance random access memory devices induced by rapid temperature annealing procedure. Applied Physics A: Materials Science and Processing, 2015, 119, 1609-1613.	1.1	5
100	Physical and chemical mechanisms in oxide-based resistance random access memory. Nanoscale Research Letters, 2015, 10, 120.	3.1	130
101	Improvement of Resistive Switching Characteristic in Silicon Oxide-Based RRAM Through Hydride-Oxidation on Indium Tin Oxide Electrode by Supercritical CO₂ Fluid. IEEE Electron Device Letters, 2015, 36, 558-560.	2.2	25
102	Mechanism of Triple Ions Effect in GeSO Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 552-554.	2.2	19
103	Galvanic Effect of Auâ€"Ag Electrodes for Conductive Bridging Resistive Switching Memory. IEEE Electron Device Letters, 2015, 36, 1321-1324.	2.2	31
104	Investigation of Hydration Reaction-Induced Protons Transport in Etching-Stop a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2015, 36, 1050-1052.	2.2	6
105	High performance, excellent reliability multifunctional graphene oxide doped memristor achieved by self-protect ive compliance current structure. , 2014, , .		5
106	Ultra-high resistive switching mechanism induced by oxygen ion accumulation on nitrogen-doped resistive random access memory. Applied Physics Letters, 2014, 105, .	1.5	24
107	Investigation of on-current degradation behavior induced by surface hydrolysis effect under negative gate bias stress in amorphous InGaZnO thin-film transistors. Applied Physics Letters, 2014, 104, .	1.5	31
108	Resistance Switching Induced by Hydrogen and Oxygen in Diamond-Like Carbon Memristor. IEEE Electron Device Letters, 2014, 35, 1016-1018.	2.2	41

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109	Ultra-violet light enhanced super critical fluid treatment in In-Ga-Zn-O thin film transistor. Applied Physics Letters, 2014, 104, .	1.5	26
110	Controllable Set Voltage in Bilayer ZnO:SiO₂/ZnO_{<italic>x</italic>} Resistance Random Access Memory by Oxygen Concentration Gradient Manipulation. IEEE Electron Device Letters, 2014, 35, 1227-1229.	2.2	12
111	Surface scattering mechanisms of tantalum nitride thin film resistor. Nanoscale Research Letters, 2014, 9, 177.	3.1	4
112	Hydrogen induced redox mechanism in amorphous carbon resistive random access memory. Nanoscale Research Letters, 2014, 9, 52.	3.1	27
113	Temperature-Dependent Instability of Bias Stress in InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2119-2124.	1.6	32
114	Tri-Resistive Switching Behavior of Hydrogen Induced Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 217-219.	2.2	23
115	Characterization of Oxygen Accumulation in Indium-Tin-Oxide for Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 630-632.	2.2	55
116	Dual Ion Effect of the Lithium Silicate Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 530-532.	2.2	41
117	Resistive Switching Modification by Ultraviolet Illumination in Transparent Electrode Resistive Random Access Memory. IEEE Electron Device Letters, 2014, 35, 633-635.	2.2	39
118	Integrated One Diodeâ€“One Resistor Architecture in Nanopillar SiO_x Resistive Switching Memory by Nanosphere Lithography. Nano Letters, 2014, 14, 813-818.	4.5	97
119	Low-power bipolar resistive switching TiN/HfO₂/ITO memory with self-compliance current phenomenon. Applied Physics Express, 2014, 7, 034101.	1.1	70
120	The resistive switching characteristics in TaON films for nonvolatile memory applications. Thin Solid Films, 2013, 528, 224-228.	0.8	14
121	N 2 O plasma treatment suppressed temperature-dependent sub-threshold leakage current of amorphous indiumâ€“galliumâ€“zinc-oxide thin film transistors. Surface and Coatings Technology, 2013, 231, 281-284.	2.2	5
122	High performance of graphene oxide-doped silicon oxide-based resistance random access memory. Nanoscale Research Letters, 2013, 8, 497.	3.1	18
123	Hopping conduction distance dependent activation energy characteristics of Zn:SiO2 resistance random access memory devices. Applied Physics Letters, 2013, 102, .	1.5	20
124	Space electric field concentrated effect for Zr:SiO2 RRAM devices using porous SiO2 buffer layer. Nanoscale Research Letters, 2013, 8, 523.	3.1	16
125	Origin of Hopping Conduction in Graphene-Oxide-Doped Silicon Oxide Resistance Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 677-679.	2.2	55
126	Endurance Improvement Technology With Nitrogen Implanted in the Interface of ${m WSiO}_{f x}$ Resistance Switching Device. IEEE Electron Device Letters, 2013, 34, 864-866.	2.2	40

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127	Hopping effect of hydrogen-doped silicon oxide insert RRAM by supercritical CO₂ fluid treatment. IEEE Electron Device Letters, 2013, 34, 617-619.	2.2	42
128	Low Temperature Improvement Method on ${m Zn{:}SiO}_{x}$ Resistive Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 511-513.	2.2	30
129	Study of high-tech process furnace using inherently safer design strategies (I) temperature distribution model and process effect. Journal of Loss Prevention in the Process Industries, 2013, 26, 1198-1211.	1.7	27
130	Atomic-level quantized reaction of HfO_x memristor. Applied Physics Letters, 2013, 102, 172903.	1.5	100
131	The effect of high/low permittivity in bilayer HfO2/BN resistance random access memory. Applied Physics Letters, 2013, 102, .	1.5	32
132	Performance and characteristics of double layer porous silicon oxide resistance random access memory. Applied Physics Letters, 2013, 102, .	1.5	41
133	Mechanical Stress Influence on Electronic Transport in Low-k SiOC Dielectric Dual Damascene Capacitor. IEEE Electron Device Letters, 2013, 34, 1056-1058.	2.2	1
134	Mechanism of power consumption inhibitive multi-layer Zn:SiO2/SiO2structure resistance random access memory. Journal of Applied Physics, 2013, 114, 234501.	1.1	11
135	Electrical conduction mechanism of Zn:SiO_x resistance random access memory with supercritical CO₂ fluid process. Applied Physics Letters, 2013, 103, 083509.	1.5	39
136	Characteristics and Mechanisms of Silicon-Oxide-Based Resistance Random Access Memory. IEEE Electron Device Letters, 2013, 34, 399-401.	2.2	62
137	Characteristics of hafnium oxide resistance random access memory with different setting compliance current. Applied Physics Letters, 2013, 103, .	1.5	44
138	Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. IEEE Electron Device Letters, 2013, 34, 502-504.	2.2	55
139	Mechanical stress influence on electronic transport in low-k SiOC dielectric single damascene capacitor. Applied Physics Letters, 2013, 102, .	1.5	6
140	N2O Plasma Treatment Suppressed Temperature-dependent Point Defects Formation with Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. ECS Transactions, 2013, 45, 47-55.	0.3	1
141	N2O Plasma Treatment Suppressed Temperature-Dependent Point Defects Formation with Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. ECS Transactions, 2012, 45, 169-178.	0.3	1
142	Suppress temperature instability of InGaZnO thin film transistors by N2O plasma treatment, including thermal-induced hole trapping phenomenon under gate bias stress. Applied Physics Letters, 2012, 100, .	1.5	38
143	Silicon introduced effect on resistive switching characteristics of WOX thin films. Applied Physics Letters, 2012, 100, 022904.	1.5	39
144	The Effect of Silicon Oxide Based RRAM with Tin Doping. Electrochemical and Solid-State Letters, 2012, 15, H65.	2.2	48

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145	Publisher's Note: The Effect of Silicon Oxide Based RRAM with Tin Doping [Electrochem. Solid-State Lett., 15, H65 (2012)]. ECS Solid State Letters, 2012, 1, X1-X1.	1.4	0
146	Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical $hbox{CO}_{2}$ Fluid Treatment. IEEE Electron Device Letters, 2012, 33, 1693-1695.	2.2	45
147	Bipolar Resistive RAM Characteristics Induced by Nickel Incorporated Into Silicon Oxide Dielectrics for IC Applications. IEEE Electron Device Letters, 2012, 33, 1696-1698.	2.2	48
148	Dehydroxyl effect of Sn-doped silicon oxide resistance random access memory with supercritical CO2 fluid treatment. Applied Physics Letters, 2012, 101, .	1.5	35
149	Asymmetric Carrier Conduction Mechanism by Tip Electric Field in $hbox{WSiO}_{X}$ Resistance Switching Device. IEEE Electron Device Letters, 2012, 33, 342-344.	2.2	33
150	Abnormal Subthreshold Leakage Current at High Temperature in InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 540-542.	2.2	10
151	Paraffin wax passivation layer improvements in electrical characteristics of bottom gate amorphous indiumâ€“galliumâ€“zinc oxide thin-film transistors. Thin Solid Films, 2011, 520, 1608-1611.	0.8	17
152	Reducing operation current of Ni-doped silicon oxide resistance random access memory by supercritical CO2 fluid treatment. Applied Physics Letters, 2011, 99, .	1.5	53
153	Improving Resistance Switching Characteristics with SiGeOx/SiGeON Double Layer for Nonvolatile Memory Applications. Electrochemical and Solid-State Letters, 2011, 14, H419.	2.2	8
154	Low-Temperature Synthesis of ZnO Nanotubes by Supercritical CO2 Fluid Treatment. Electrochemical and Solid-State Letters, 2011, 14, K47.	2.2	18
155	Redox Reaction Switching Mechanism in RRAM Device With $hbox{Pt/CoSiO}_{X}hbox{/}hbox{TiN}$ Structure. IEEE Electron Device Letters, 2011, 32, 545-547.	2.2	120
156	A low-temperature method for improving the performance of sputter-deposited ZnO thin-film transistors with supercritical fluid. Applied Physics Letters, 2009, 94, .	1.5	72
157	Improvement of the performance of ZnO TFTs by low-temperature supercritical fluid technology treatment. Surface and Coatings Technology, 2009, 204, 1112-1115.	2.2	12